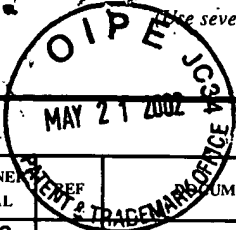


INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

BOW5075.1

Application Number

10/051,623

Applicant(s)

BOWER, ROBERT W.

Filing Date

JANUARY 17, 2002

Group Art Unit

2813 2829

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EP		5,374,564	12/1994	Bruel	—	—	
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BOW5075.01

10/051,623

BOWER, ROBERT W.

JANUARY 17, 2002

2813 2829

PATENT & TRADEMARK OFFICE

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Applicant(s)

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